- TLV431 Precision Programmable Reference (1.24 V) and an Optocoupler in a Single Package
- 1% Voltage-Reference Tolerance
- Controlled Optocoupler CTRs:

TPS5908, TPS5910 100% to 400% TPS5908A, TPS5910A 150% to 300%

- High Withstand Voltage (WTV), 7500 V Peak for 1 Minute
- Safety Regulatory Approvals
 - UL... File Number E65085
 - FIMKO, SEMKO, NEMKO, DEMKO
 - EN60065/IEC 65
 - EN60950/IEC 950
 - VDE 0884, Level 4 (6000-V Insulation)

DCS OR P PACKAGE (TOP VIEW) LED [1 8 NC/BASE† COMP [2 7 C GND [3 6] E FB [4 5 NC NC – No internal connection

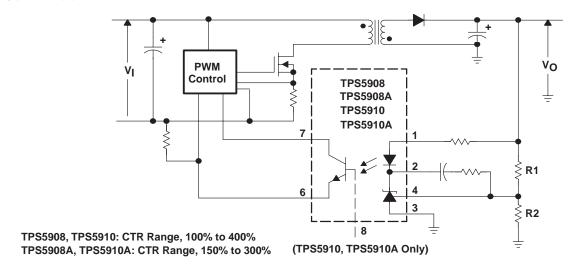
NC – No internal connection †BASE – TPS5910, TPS5910A only

description

These optoisolated feedback amplifiers consist of the industry standard TLV431 precision programmable reference with a 1% reference voltage tolerance, and an optocoupler. The devices are primarily intended for use as the error-amplifier/reference/isolation-amplifier element in isolated ac-to-dc power supplies and dc-to-dc converters. The optocoupler is a gallium-arsenide (GaAs) light-emitting diode that emits at a wavelength of 940 nm, combined with a silicon phototransistor. The current transfer ratio (CTR) ranges from 100% to 400% in the standard version. The TPS5908A and TPS5910A versions with 150%-to-300% CTR are available for higher-performance applications. All versions enable power-supply designers to reduce component count and save space in tightly packaged designs. The tight-tolerance reference eliminates the need for adjustments in many applications.

These devices are characterized for operation from –40°C to 100°C. Each amplifier is supplied in an 8-pin DIP or in an 8-pin gull-wing surface-mount package (DCS).

typical application

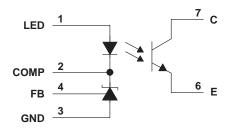




Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



schematic



Terminal Functions

TERMINAL			DESCRIPTION					
NAME	NO.	1/0	DESCRIPTION					
С	7		Phototransistor collector					
COMP	2	0	emitting diode and TLV431 cathodes					
Е	6		Phototransistor emitter					
FB	4	I	Feedback					
GND	3		Ground					
LED	1	I	Light-emitting diode anode					
NC	5, 8		No connection					

absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)†

Input power dissipation at (or below) T _A = 25°C (see Note 1)	250 mW
Input LED current, I _{I(LED)}	50 mA
Input LED voltage, $\hat{V}_{I(LED)}$	
Input diode reverse voltage	
Output power dissipation at (or below) T _A = 25°C (see Note 2)	150 mW
Output collector-to-emitter voltage	35 V
Output emitter-to-collector voltage	7 V
Output collector current	50 mA
Total continuous power dissipation at (or below) $T_A = 25^{\circ}C$ (see Note 3)	350 mW
Operating free-air temperature range, T _A	40°C to 100°C
Storage temperature range, T _{stq}	–55°C to 150°C
Total input-to-output voltage	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C
Flammability	(see Note 4)

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. Derate linearly from 25°C at a rate of 2.95 mW/°C.
 - 2. Derate linearly from 25°C at a rate of 1.76 mW/°C.
 - 3. Derate linearly from 25°C at a rate of 4.12 mW/°C.
 - 4. Optocoupler total-package flame retardancy is tested to IEC695-2-2 using a flame application time of 30 seconds. Outer mold compound is verified to meet UL 94 V-0.



electrical characteristics, $T_A = 25^{\circ}C$ (unless otherwise noted)

input

PARAMETER		TEST CONDITI	MIN	TYP	MAX	UNIT	
VF	Light-emitting diode forward voltage	VO(COMP) = VI(FB), See Figure 1	$I_{I(LED)} = 10 \text{ mA},$		1.2	1.4	V
I _R	Light-emitting diode reverse current	V _R = 6 V				10	μΑ
V _{ref}	Reference voltage	VO(COMP) = VI(FB), See Figure 1	$I_{I(LED)} = 10 \text{ mA},$	1.228	1.24	1.252	V
V _{ref(dev)}	Deviation of reference voltage over temperature	VO(COMP) = VI(FB), T _A = 25°C to 100°C,	I _{I(LED)} = 10 mA, See Figure 1		4		mV
$\frac{\Delta V_{ref}}{\Delta V_{I(LED)}}$	Ratio of reference voltage change-to-change in input light-emitting-diode voltage	$\Delta V_{I(LED)} = 3 \text{ V to 7 V},$ See Figure 2	$I_{I(LED)} = 10 \text{ mA},$		-1.5	-2.7	mV/V
I _I (FB)	Feedback input current	I _{I(LED)} = 10 mA, See Figure 3	$R3 = 10 \text{ k}\Omega$,		0.15	0.5	μΑ
I _{ref(dev)}	Deviation of reference input current over temperature	I _I (LED) = 10 mA, T _A = 25°C to 100°C,	R3 = 10 kΩ, See Figure 3		0.05		μΑ
I _{DRV(min)}	Minimum drive current	VO(COMP) = VI(FB),	See Figure 1		55	80	μΑ
I _{I(off)}	Off-state input light-emitting-diode current	V _{I(LED)} = 7 V, See Figure 4	$V_{I(FB)} = 0$,		0.001	0.1	μΑ
Z _{ka} †	Regulator output impedance	VO(COMP) = VI(FB), IO(COMP) = 1 mA to 50 mA	$f \le 1 \text{ kHz},$		0.25	·	Ω

[†] This symbol is not currently listed within EIA or JEDEC standards for semiconductor symbology.

output

PARAMETER			TEST CONDITIONS		MIN	TYP	MAX	UNIT
ICEO	Collect dark current	V _{CE} = 35 V,	See Figure 5			100	nA	
V(BR)ECO	Breakdown voltage, emitter-to-collector, base or	I _E = 100 μA		7			V	
V _(BR) CBO	Breakdown voltage, collector-to-base, emitter open		$I_C = 10 \mu A$, See Figure 7	I _F = 0,	70			V
h _{FE}	Static forward current transfer ratio, common collector	TPS5910, TPS5910A	$I_C = 10 \text{ mA},$ $I_F = 0,$	V _{CE} = 5 V, See Figure 8	200			
V _{(BR)EBO}	Breakdown voltage, emitter-to-base, collector open		I _E = 10 μA, See Figure 9	IF = 0,	7			V

coupler

	PARAMETER	TEST CON	MIN	TYP	MAX	UNIT		
CTR	Current transfer ratio	TPS5908, TPS5910	$V_{O(COMP)} = V_{I(FB)}$	I _{I(I FD)} = 5 mA,	100%		400%	
	Current transfer ratio	TPS5908A, TPS5910A	V _{CE} = 5 V,	I _I (LED) = 5 mA, See Figure 6	150%		300%	
V _{CE(sat)}	Collector-emitter saturation voltage	$V_{O(COMP)} = V_{I(FB)}$, $I_{C} = 1 \text{ mA}$,	I _{I(LED)} = 10 mA, See Figure 6		0.1	0.2	V	
v _{iso} †	Isolation voltage		I _{IO} = 10 μA,	f = 60 Hz	7500			V
C _{io}	Input to output capacitance	V _{IO} = 0,	f = 1 kHz		0.6		pF	

[†] This symbol is not currently listed within EIA or JEDEC standards for semiconductor symbology.



PARAMETER MEASUREMENT INFORMATION

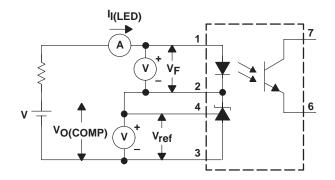


Figure 1. V_{ref} , V_{F} , I_{min} Test Circuit

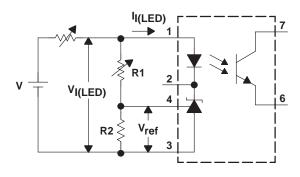


Figure 2. $\Delta V_{ref}/\Delta V_{I(LED)}$ Test Circuit

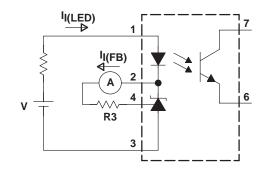


Figure 3. I_{I(FB)} Test Circuit

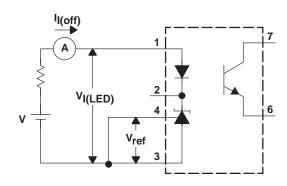


Figure 4. I_{I(off)} Test Circuit

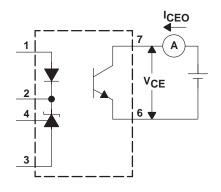


Figure 5. I_{CEO} Test Circuit

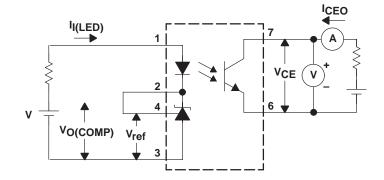
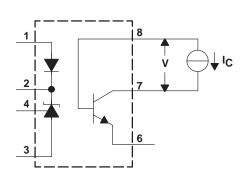


Figure 6. CTR, V_{CE(sat)} Test Circuit

PARAMETER MEASUREMENT INFORMATION



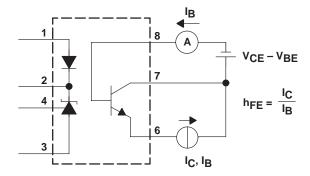


Figure 7. V_{(BR)CBO} Test Circuit

Figure 8. hFE Test Circuit

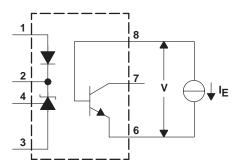


Figure 9. V_{(BR)EBO} Test Circuit

TYPICAL CHARACTERISTICS

INPUT LIGHT-EMITTING-DIODE CURRENT VS REFERENCE VOLTAGE VO(COMP) = VI(FB) TA = 25°C 150 0 0 0.5 1 1.5 Vref - Reference Voltage - V

Figure 10

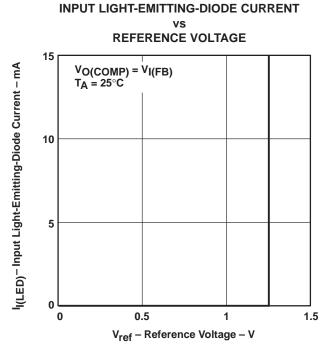


Figure 11

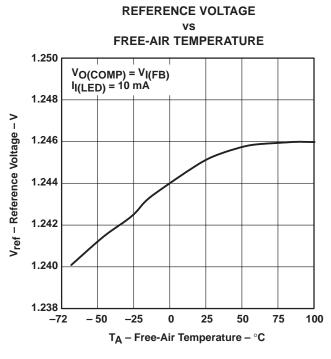


Figure 12

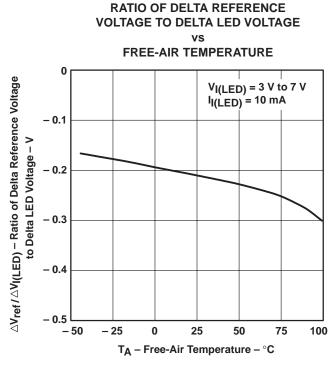


Figure 13

TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

TYPICAL CHARACTERISTICS

Figure 14

Figure 16

 T_A – Free-Air Temperature – $^{\circ}$ C

OFF-STATE INPUT LIGHT-EMITTING-DIODE CURRENT vs FREE-AIR TEMPERATURE

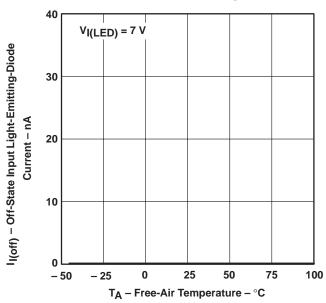


Figure 15

NORMALIZED CURRENT TRANSFER RATIO RELATIVE TO VALUE AT $T_A = 25^{\circ}C$

vs FREE-AIR TEMPERATURE

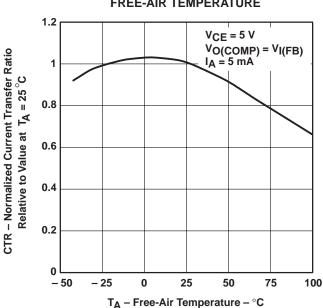


Figure 17



TYPICAL CHARACTERISTICS

CURRENT TRANSFER RATIO VS INPUT LIGHT-EMITTING-DIODE CURRENT 300 VCE = 5 V 250 150 100 1 2 3 5 10 20 30 50 Il(LED) - Input Light-Emitting-Diode Current - mA

COLLECTOR-TO-EMITTER SATURATION VOLTAGE

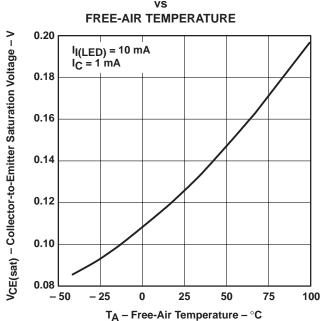


Figure 18 Figure 19

INPUT LIGHT-EMITTING-DIODE FORWARD CURRENT

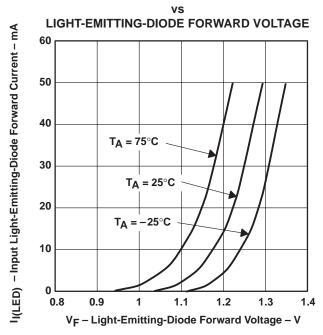
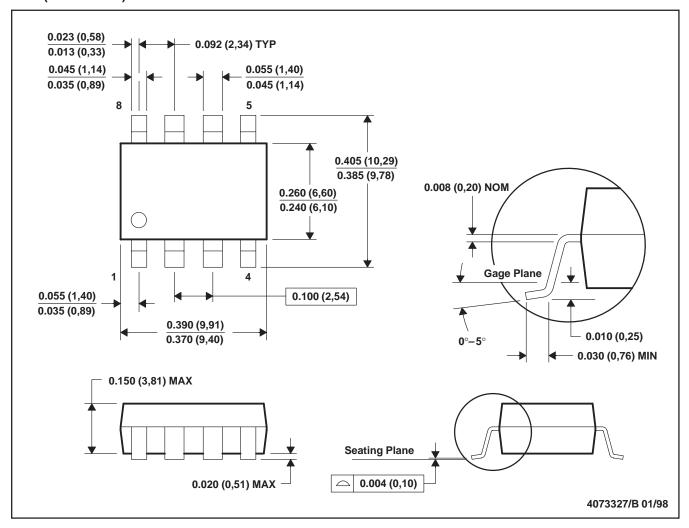


Figure 20

MECHANICAL DATA

DCS (R-PDSO-G8)

PLASTIC DUAL SMALL-OUTLINE OPTO COUPLER



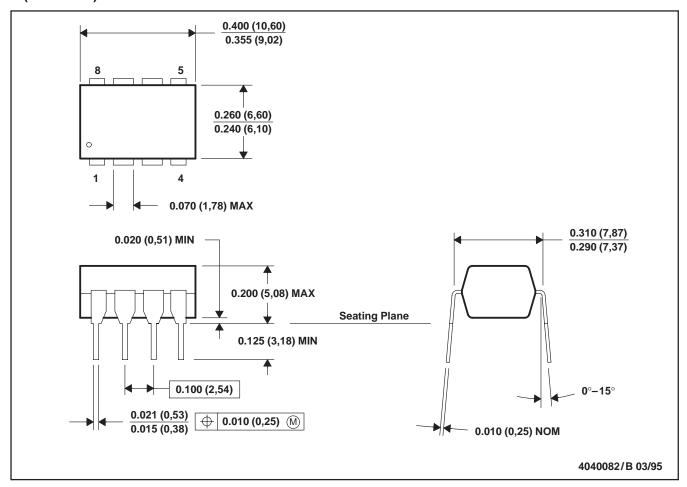
 $\label{eq:NOTES:A.All linear dimensions are in inches (millimeters).}$

B. This drawing is subject to change without notice.

MECHANICAL DATA

P (R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Falls within JEDEC MS-001

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 1998, Texas Instruments Incorporated